AON7900

30V Dual Asymmetric N-Channel MOSFET

General Description

The AON7900 is designed to provide a high efficiency synchronous buck power stage with optimal layout and board space utilization. It includes two specialized MOSFETs in a dual Power DFN3.3x3.3 package. The Q1 "High Side" MOSFET is designed to minimize switching losses. The Q2 "Low Side" MOSFET is designed for low $R_{DS(ON)}$ to reduce conduction losses. The AON7900 is well suited for use in compact DC/DC converter applications.

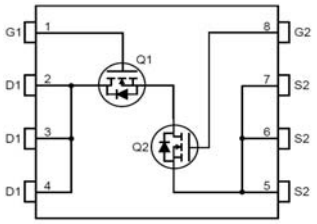
Product Summary

	Q1	Q2
V_{DS}	30V	30V
I_D (at V_{GS}=10V)	24A	40A
$R_{DS(ON)}$ (at V_{GS}=10V)	<21mΩ	<6.7mΩ
$R_{DS(ON)}$ (at V_{GS} = 4.5V)	<28mΩ	<8.5mΩ

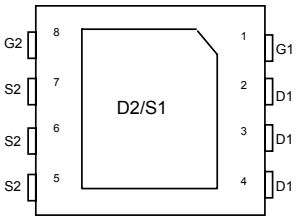
100% UIS Tested
100% Rg Tested

Green Product

Top View



Bottom View



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	±20		V
Continuous Drain Current [G]	T_C=25°C	I_D	24	40	A
	T_C=100°C		15	31	
Pulsed Drain Current [C]		I_{DM}	90	150	
Continuous Drain Current	T_A=25°C	I_{DSM}	8	13	A
	T_A=70°C		6	10	
Avalanche Current [C]		I_{AS}, I_{AR}	22	28	A
Avalanche Energy L=0.1mH [C]		E_{AS}, E_{AR}	24	39	mJ
Power Dissipation [B]	T_C=25°C	P_D	17	50	W
	T_C=100°C		7	20	
Power Dissipation [A]	T_A=25°C	P_{DSM}	1.8	1.8	W
	T_A=70°C		1.1	1.1	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics

Parameter		Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	27	27	35	35	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		60	60	72	72	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	6	2	7.5	2.5	°C/W

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1.3	1.8	2.3	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	90			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=8A		17	21	mΩ
		T_J=125°C		24	29	
		V_{GS}=4.5V, I_D=4A		22	28	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=8A		33		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.7		V
I_S	Maximum Body-Diode Continuous Current				20	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz	470	590	710	pF
C_{oss}	Output Capacitance		250	360	450	pF
C_{rss}	Reverse Transfer Capacitance		13	23	40	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.7	1.5	2.3	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=8A	7	9	11	nC
Q_g(4.5V)	Total Gate Charge		3	4	5	nC
Q_{gs}	Gate Source Charge			1.6		nC
Q_{gd}	Gate Drain Charge			1.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=1.8Ω, R_{GEN}=3Ω		6		ns
t_r	Turn-On Rise Time			3		ns
$t_{D(off)}$	Turn-Off DelayTime			18		ns
t_f	Turn-Off Fall Time			3		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=8A, dI/dt=500A/µs	8	11	14	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=8A, dI/dt=500A/µs	15	19	23	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

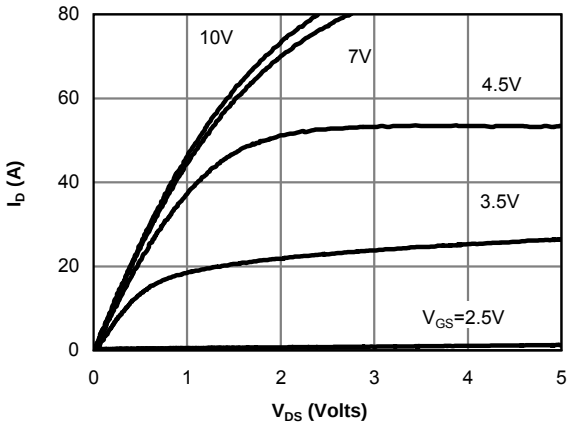


Fig 1: On-Region Characteristics (Note E)

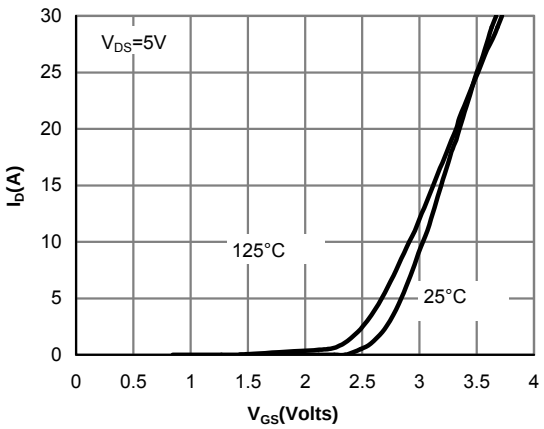


Figure 2: Transfer Characteristics (Note E)

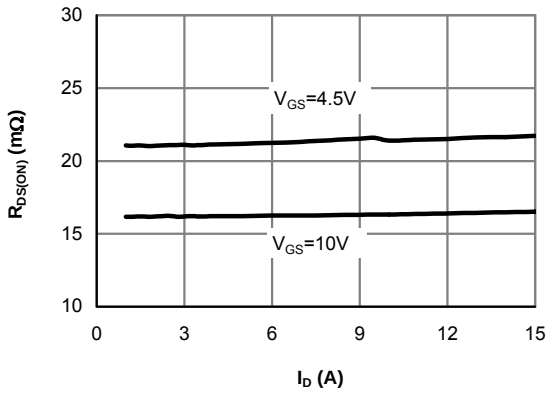


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

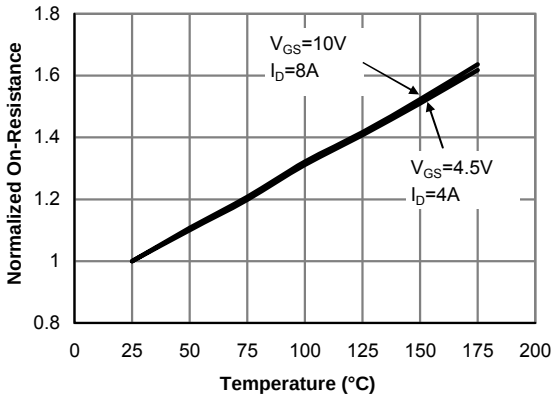


Figure 4: On-Resistance vs. Junction Temperature (Note E)

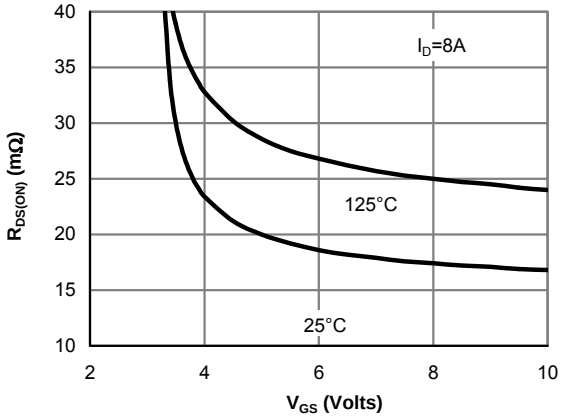


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

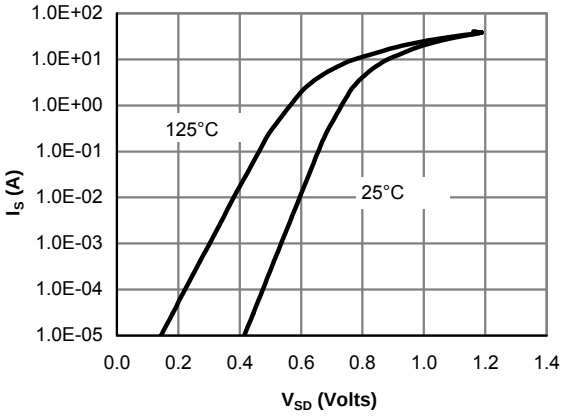


Figure 6: Body-Diode Characteristics (Note E)

Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

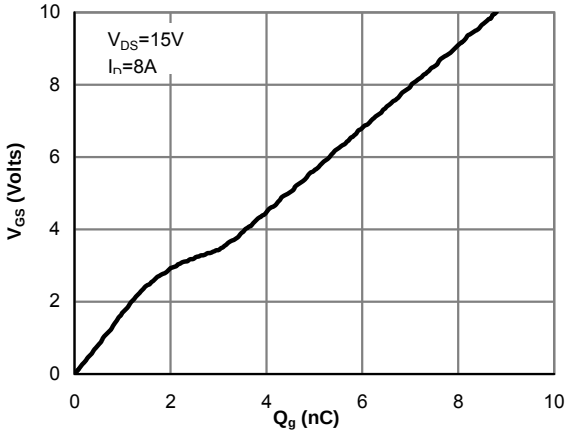


Figure 7: Gate-Charge Characteristics

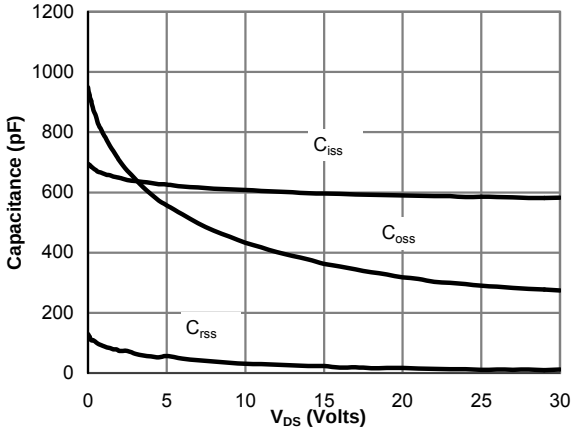


Figure 8: Capacitance Characteristics

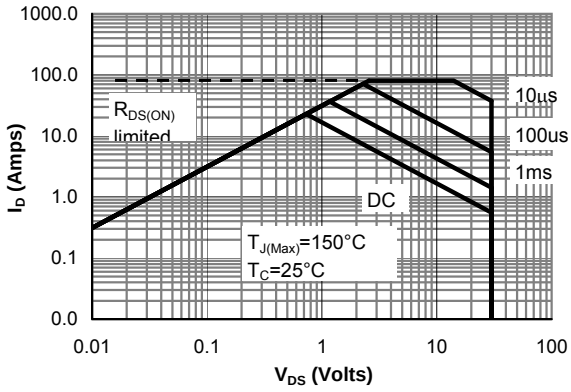


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

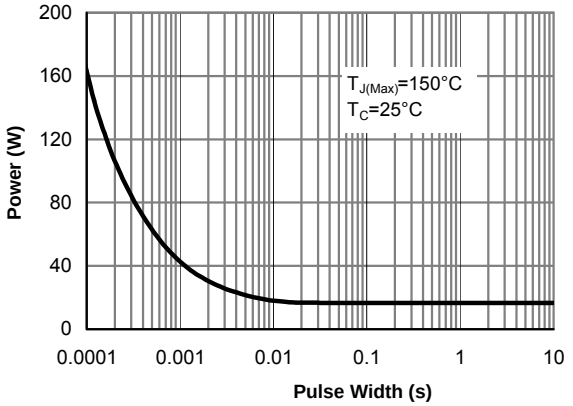


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

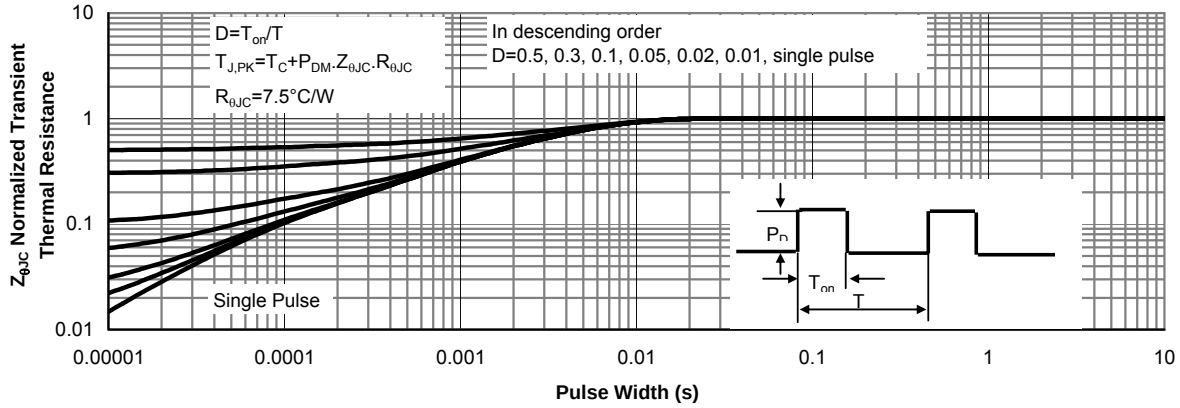


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

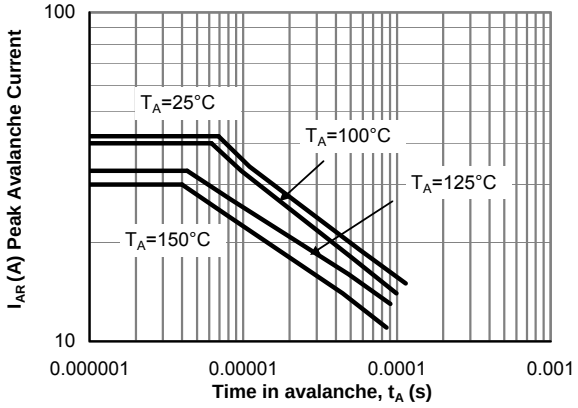


Figure 12: Single Pulse Avalanche capability (Note C)

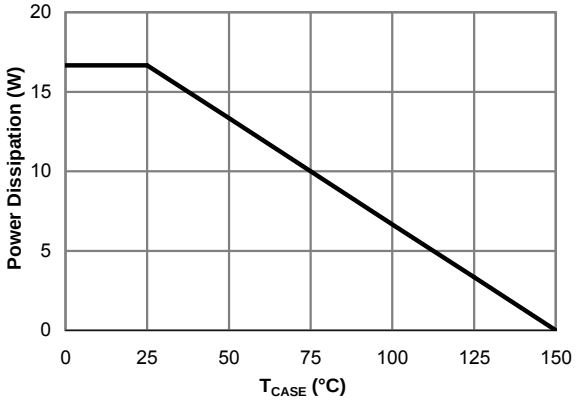


Figure 13: Power De-rating (Note F)

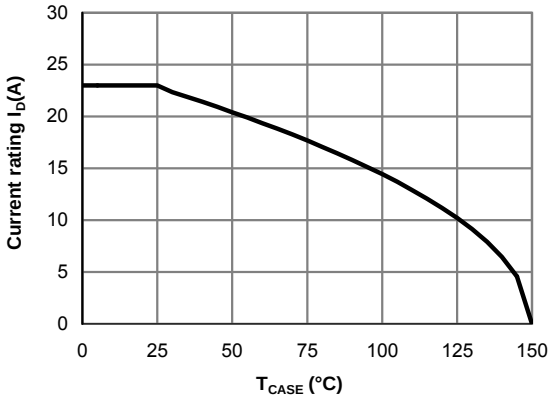


Figure 14: Current De-rating (Note F)

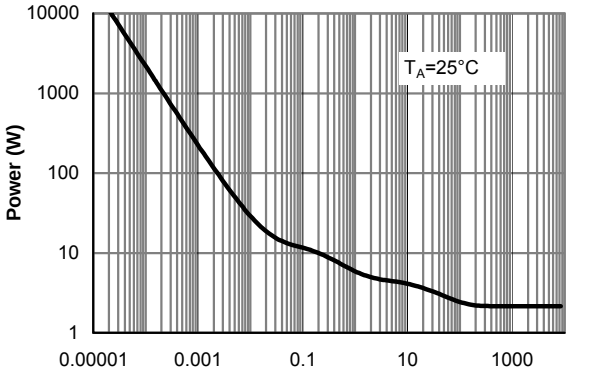


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

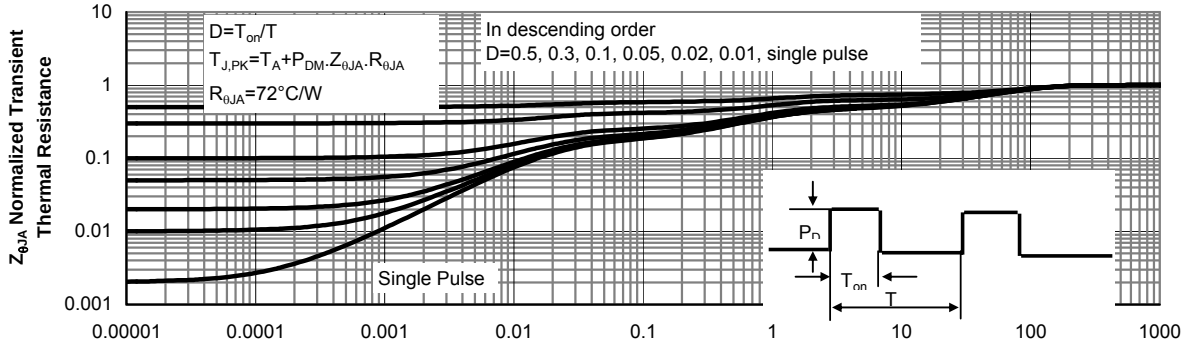


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1.3	1.8	2.3	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	150			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=13A		5.5	6.7	mΩ
		T_J=125°C		7.5	9	
		V_{GS}=4.5V, I_D=10A		6.7	8.5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=13A		50		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.7		V
I_S	Maximum Body-Diode Continuous Current[G]				40	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz	1400	1770	2130	pF
C_{oss}	Output Capacitance		580	830	1080	pF
C_{rss}	Reverse Transfer Capacitance		43	72	120	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.7	1.4	2.1	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=13A	21	27	33	nC
Q_g(4.5V)	Total Gate Charge		9	12	15	nC
Q_{gs}	Gate Source Charge			4		nC
Q_{gd}	Gate Drain Charge			5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=1.2Ω, R_{GEN}=3Ω		7		ns
t_r	Turn-On Rise Time			3		ns
$t_{D(off)}$	Turn-Off DelayTime			27		ns
t_f	Turn-Off Fall Time			6		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=13A, dI/dt=500A/µs	13	17	21	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=13A, dI/dt=500A/µs	27	34	41	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.

G. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

O2-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

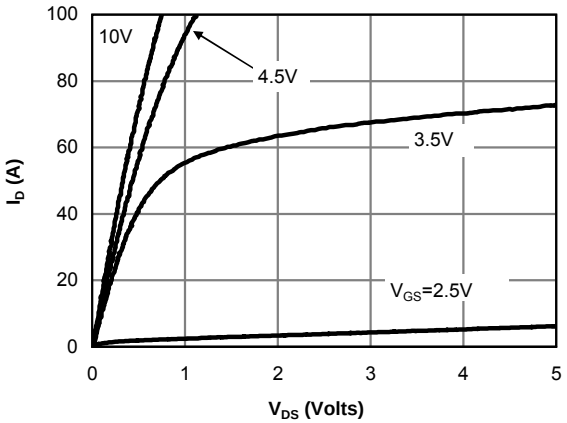


Fig 1: On-Region Characteristics (Note E)

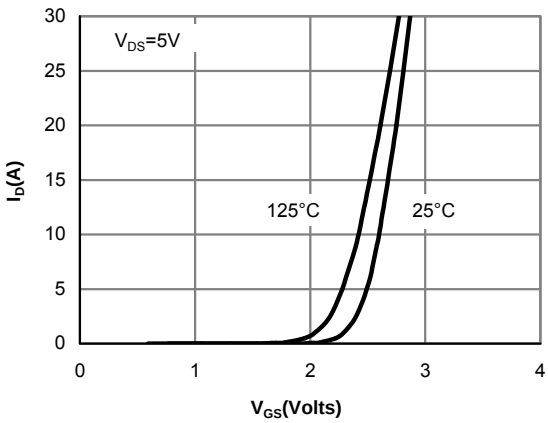


Figure 2: Transfer Characteristics (Note E)

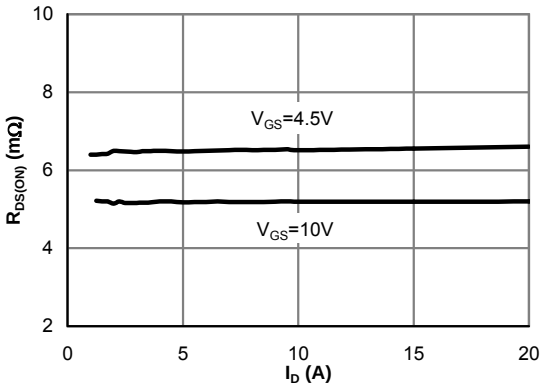


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

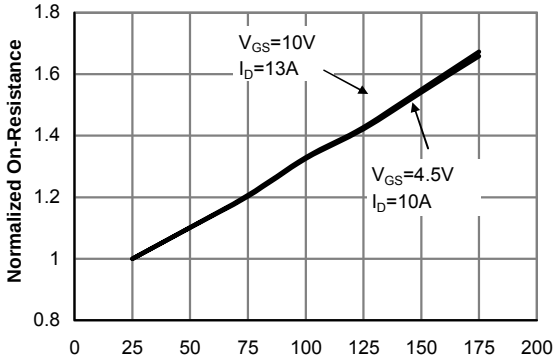


Figure 4: On-Resistance vs. Junction Temperature (Note E)

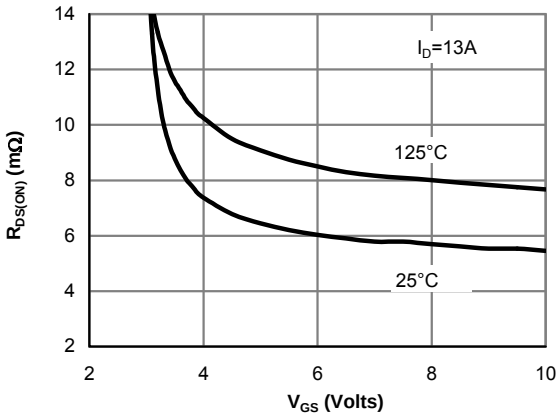


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

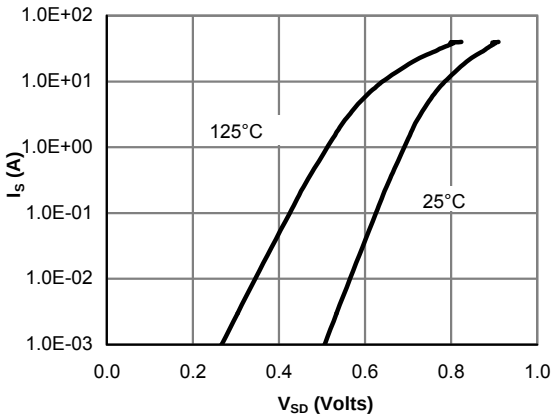


Figure 6: Body-Diode Characteristics (Note E)

Q2-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

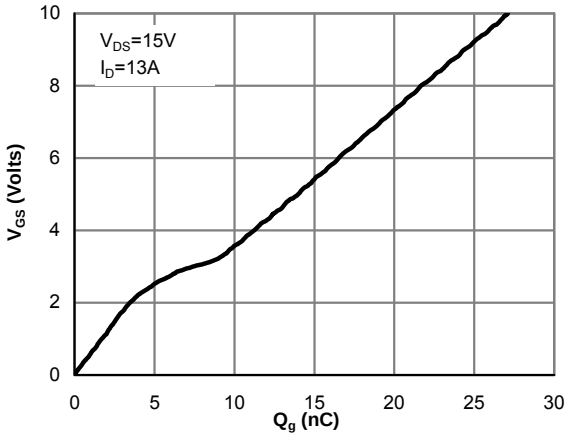


Figure 7: Gate-Charge Characteristics

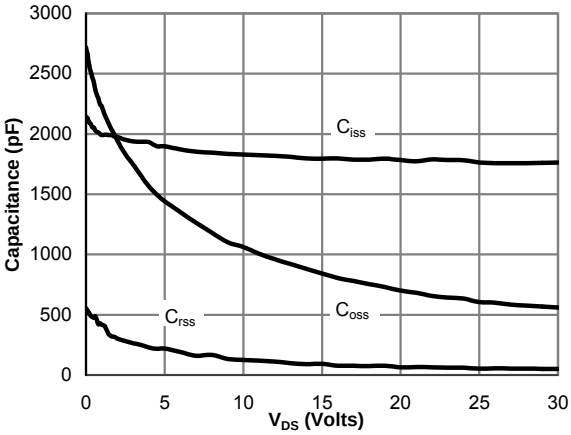


Figure 8: Capacitance Characteristics

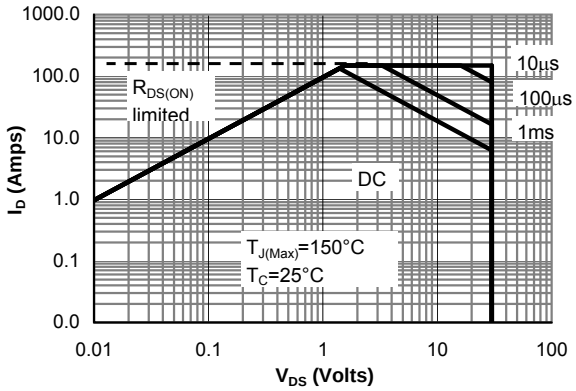


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

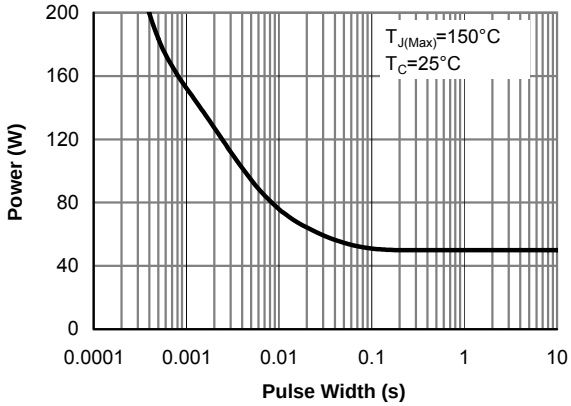


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

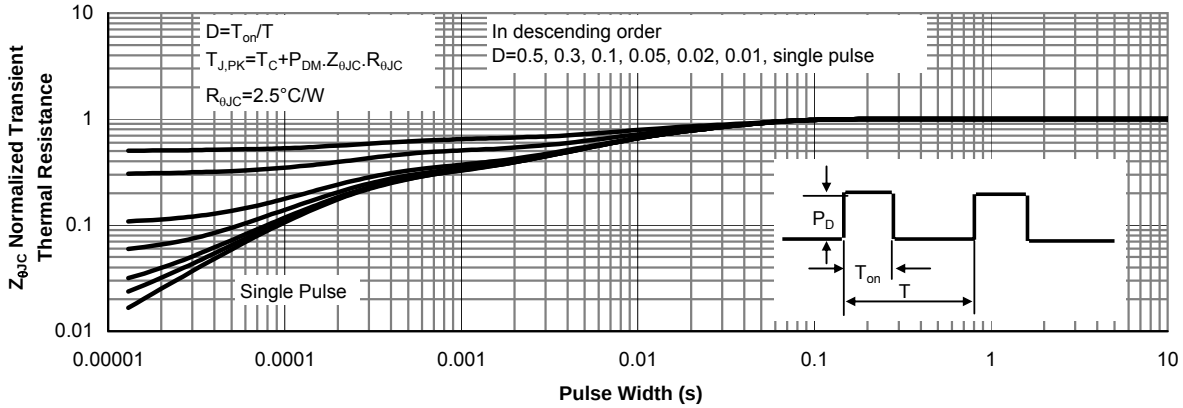


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Q2-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

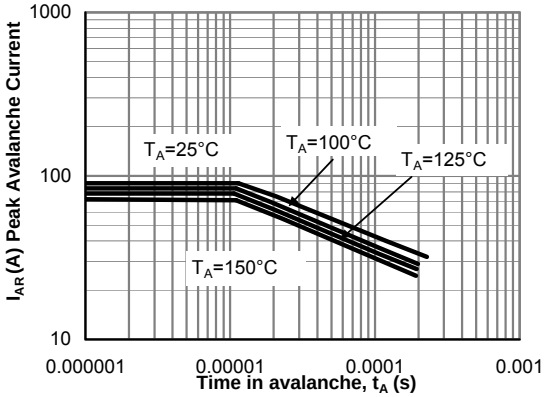


Figure 12: Single Pulse Avalanche capability (Note C)

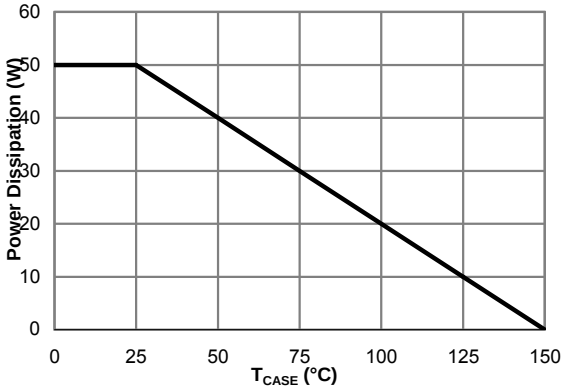


Figure 13: Power De-rating (Note F)

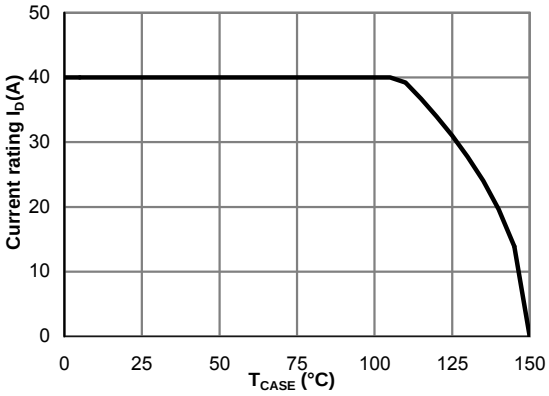


Figure 14: Current De-rating (Note F)

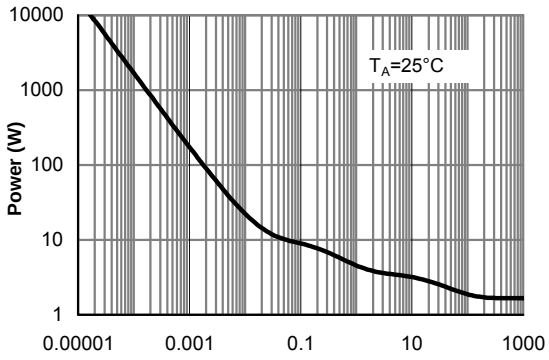


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note G)

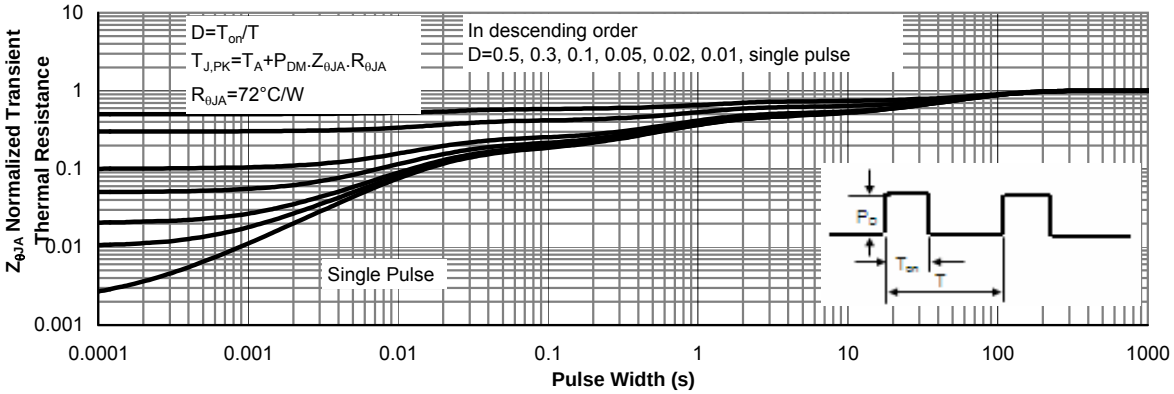
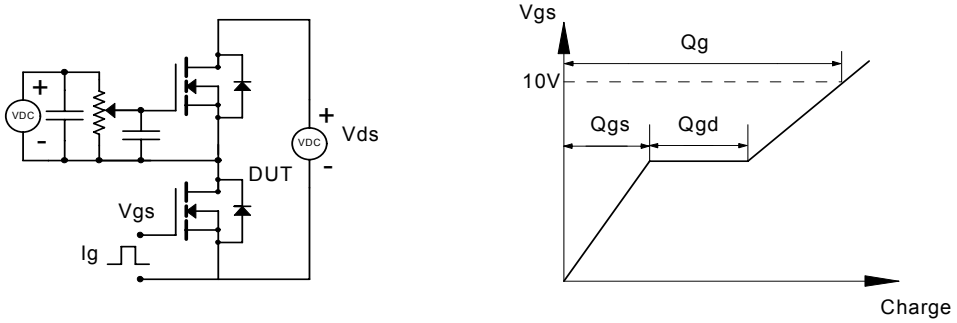
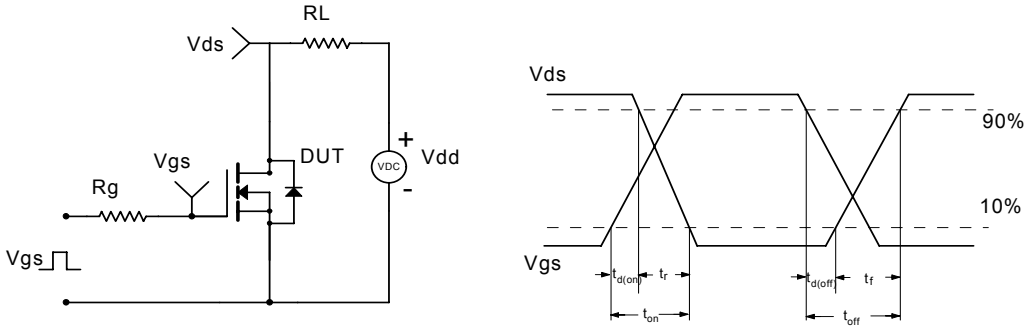


Figure 16: Normalized Maximum Transient Thermal Impedance (Note G)

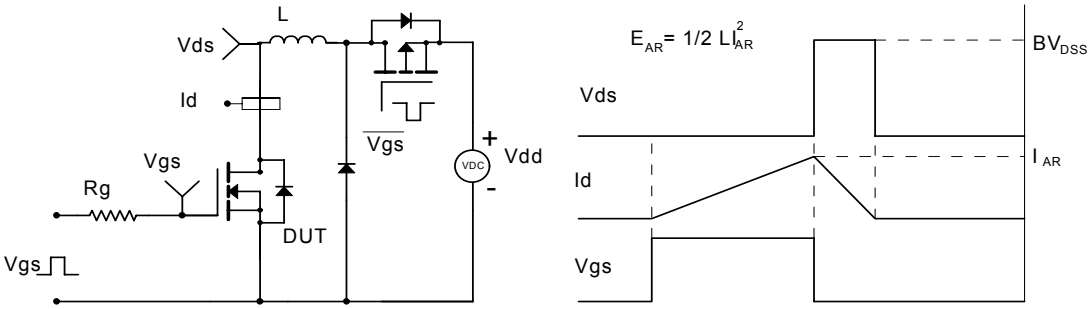
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms